Symmetrical Gate Turn-Off Thyristor Type SA20AP1200UK



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### **Absolute Maximum Ratings**

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V <sub>DRM</sub>	Repetitive peak off-state voltage, (note 1)	2000	V
V <sub>RSM</sub>	Non-repetitive peak off-state voltage, (note 1)	2100	V
V <sub>RRM</sub>	Repetitive peak reverse voltage	1000	V
V <sub>RSM</sub>	Non-repetitive peak reverse voltage	1000	V
note 1)	$V_{GK} = -2V$		

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
I <sub>TGQ</sub>	Peak turn-off current (note 1)	1200	А
L <sub>S</sub>	Snubber loop impedance, $I_{TM} = I_{TGQ}$ (note 1)	0.3	μΗ
I <sub>T(AV)M</sub>	Mean on-state current, T <sub>sink</sub> = 55°C, (note 2)	670	А
I <sub>T(RMS)</sub>	Nominal RMS on-state current, T <sub>sink</sub> = 25°C (note 2)	1340	А
I <sub>TSM</sub>	Peak non-repetitive surge current t <sub>p</sub> = 10ms	10.5	kA
I <sub>TSM2</sub>	Peak non-repetitive surge current (note 3)	19	kA
l <sup>2</sup> t	$I^{2}t$ capacity for fusing $t_{p}$ = 10ms	550 · 10 <sup>3</sup>	A <sup>2</sup> s
(di/dt) <sub>cr</sub>	Critical rate of rise of on-state current, (note 4)	1000	A/µs
P <sub>FGM</sub>	Peak forward gate power	210	W
P <sub>RGM</sub>	Peark reverse gate power	8	kW
I <sub>FGM</sub>	Peak forward gate current	140	A
V <sub>RGM</sub>	Peak reverse gate voltage (note 5)	18	V
t <sub>off</sub>	Minimum permissible off-time, $I_{TM} = I_{TGQ}$ (note 1)	80	μs
t <sub>on</sub>	Minimum permissible off-time	20	μs
Т <sub>јор</sub>	Operating temperature range	-40 to +125	°C
T <sub>stg</sub>	Storage temperature range	-40 to +150	°C
note 1)	$T_j$ = 125°C, $V_D$ = 80% $V_{DM}$ , $V_{DM} ≤ V_{DRM}$ , $di_{GQ}/dt$ = 20A/µs, $C_S$ = 3µF		
note 2)	Double-side cooled, single phase, 50Hz, 180° half-sinewave.		
note 3)	Half-sinewave, t <sub>p</sub> = 2ms		
note 4)	For di/dt > 1000A/µs please consult factory.		
note 5)	May exceed this value during turn-off avalanche period.		

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### Characteristics

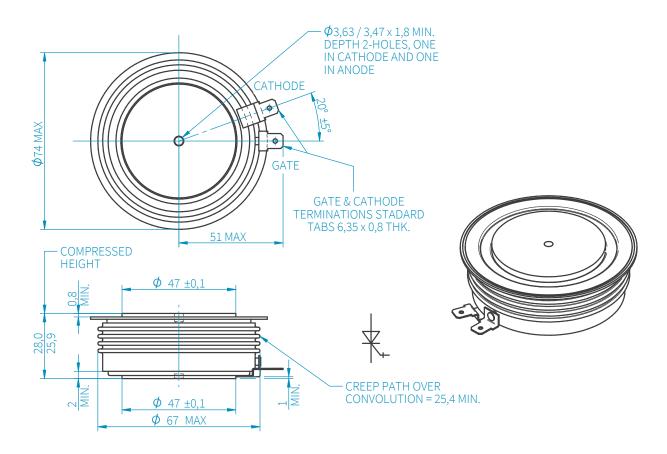
	PARAMETER	TEST CONDITIONS	MIN	ТҮР	МАХ	UNITS
V <sub>TM</sub>	Maximum peak on-state voltage	I <sub>G</sub> = 2A, I <sub>T</sub> = 1200A	-	3.0	3.3	V
IL	Latching current	T <sub>i</sub> = 25°C	-	15	-	А
Ι <sub>Η</sub>	Holding current	1 <sub>j</sub> - 25 C	-	15	-	А
(dv/dt) <sub>cr</sub>	Critical rate of rise of off-state voltage	$V_{\rm D}=80\% V_{\rm DRM}, V_{\rm GR}=-2V$	1000	-	-	V/µs
I <sub>DRM</sub>	Peak off-state current	Rated $V_{DRM}$ , $V_{GR} = -2V$	-	-	50	mA
I <sub>RRM</sub>	Peak reverse current	Rated V <sub>RRM</sub>	-	-	100	mA
I <sub>GKM</sub>	Peak negative gate leakage current	$V_{GR} = -16V$	-	-	200	mA
		$T_j$ = -40°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	1.0	-	V
V <sub>GT</sub>	Gate trigger voltage	$T_j$ = 25°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	0.9	-	V
		$T_j$ = 125°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	0.8	-	V
		$T_j$ = -40°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	3.0	8.0	А
$I_{GT}$	Gate trigger current	$T_j$ = 25°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	0.6	2.5	А
		$T_j$ = 125°C, $V_D$ = 25V, $R_L$ = 25m $\Omega$	-	60	500	mA
t <sub>d</sub>	Delay time	(note 2)	-	1.0	-	μs
t <sub>gt</sub>	Turn-on time	Conditions as for $t_d, (10\% I_{GM} \mbox{ to } 10\% V_D)$	-	3.0	7.0	μs
t <sub>f</sub>	Fall time	(note 3)	-	0.8	-	μs
t <sub>gq</sub>	Turn-off time	Conditions as for $t_f,(10\% I_{GQ} \text{ to } 10\% I_{TGQ})$	-	12	13	μs
I <sub>GQ</sub>	Turn-off gate current	Conditions as for t <sub>f</sub>	-	250	-	А
$Q_{GQ}$	Turn-off gate charge		-	1600	2000	mC
t <sub>tail</sub>	Tail time	Conditions as for $t_{\rm f},(10\% I_{\rm TGQ}$ to $I_{\rm TGQ}$ < 1A)	-	40	60	μs
t <sub>gw</sub>	Gate off-time (note 4)	Conditions as for t <sub>f</sub>	150	-	-	μs
		Double side cooled	-	-	0.027	K/W
R <sub>thJK</sub>	Thermal resistance, junction to sink	Cathode side cooled	-	-	0.070	K/W
		Anode side cooled	-	-	0.045	K/W
F	Mounting force	(note 5)	15	-	25	kN
Wt	Weight		-	480	-	g
note 1)	Unless otherwise indicated T <sub>j</sub> = 125°C					
note 2)	$V_D = 50\% V_{DRM}$ , $I_{TGQ} = 1200A$ , $I_{GM} = 40A$ , $di_G/dt = 20A/\mu s$ , $T_j = 25^{\circ}C$ , $di/dt = 300A/\mu s$ , $(10\% I_{GM} to 90\% V_D)$					
note 3)	$V_{D}$ = 80% $V_{DRM}$ , $I_{TGQ}$ = 1200A, $C_{S}$ = 3 $\mu$ F, $di_{G}/dt$ = 40A/ $\mu$ s, $V_{GR}$ = –16V, (90% $I_{TGQ}$ to 10% $V_{D}$ )					
note 4)	The gate off-time is the period during which the gate circuit is required to remain low impedance to allow for the pas- sage of tail current.					
note 5)	For other clamping forces, consult factory.					

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